

Features

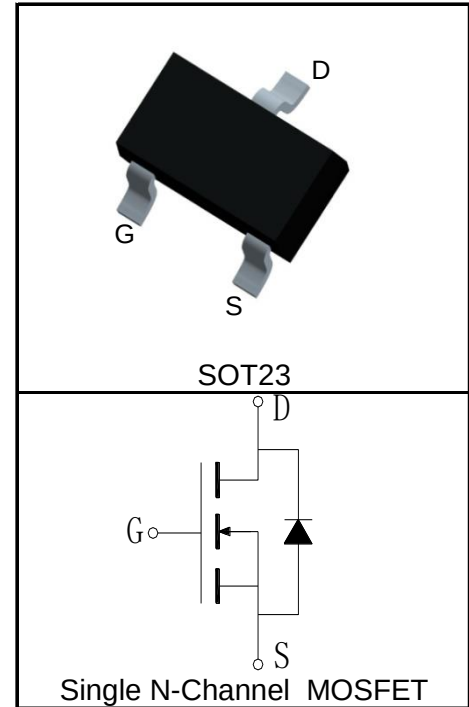
- 40V/4A,
 $R_{DS(ON)} = 30m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 40m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

Applications

- Load Switch



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _A =25°C	1.3	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _A =25°C	16	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _A =25°C	4	A
		T _A =70°C	3.2	
P _D	Maximum Power Dissipation	T _A =25°C	1	W
		T _A =70°C	0.64	
R _{θJC}	Thermal Resistance-Junction to Case		-	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		125	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		TBD	mJ

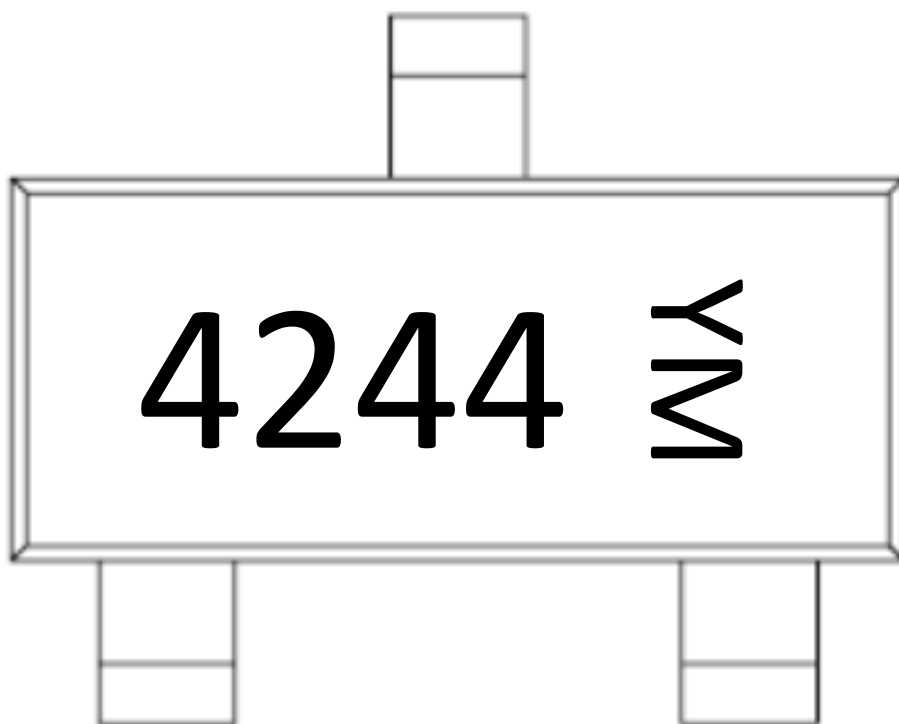
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS4244AA			Unit
			Min.	Typ.	Max.	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.5	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =4A		30	40	mΩ
		V _{GS} =4.5V, I _{DS} =3A		40	60	mΩ
Diode Characteristics						
V _{SD} ⑤	Diode Forward Voltage	I _{SD} =4A, V _{GS} =0V		0.85	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =4A, dI _{SD} /dt=100A/μs		14		ns
Q _{rr}	Reverse Recovery Charge			23		nC
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.8		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz		420		pF
C _{oss}	Output Capacitance			70		
C _{rss}	Reverse Transfer Capacitance			45		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, I _{DS} =4A, V _{GEN} =10V, R _G =6Ω		8		ns
t _r	Turn-on Rise Time			13		
t _{d(OFF)}	Turn-off Delay Time			26		
t _f	Turn-off Fall Time			9		
Gate Charge Characteristics ⑥						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =4A		13		nC
Q _{gs}	Gate-Source Charge			3.5		
Q _{gd}	Gate-Drain Charge			4.2		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} . Starting $T_J = 25^{\circ}\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

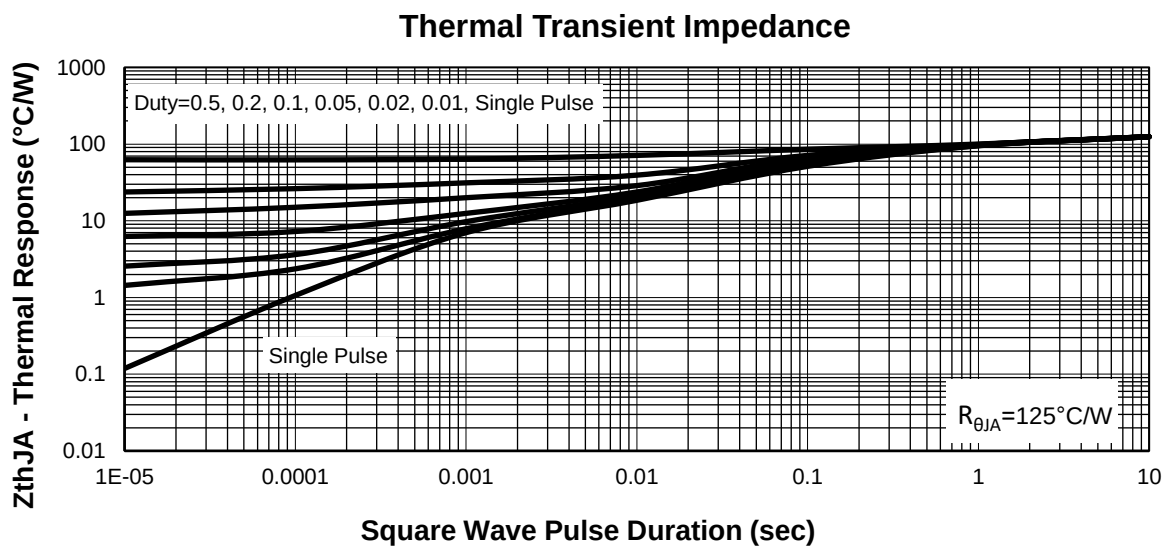
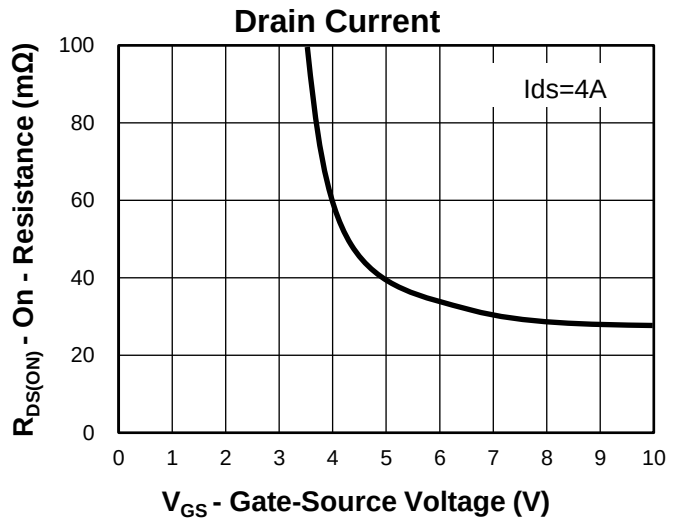
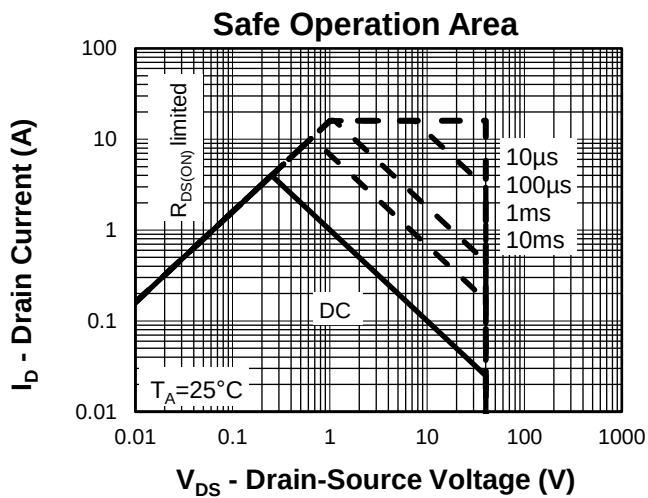
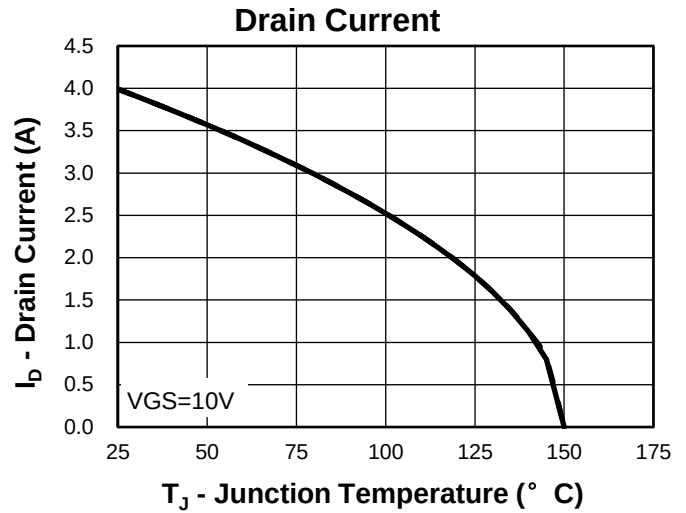
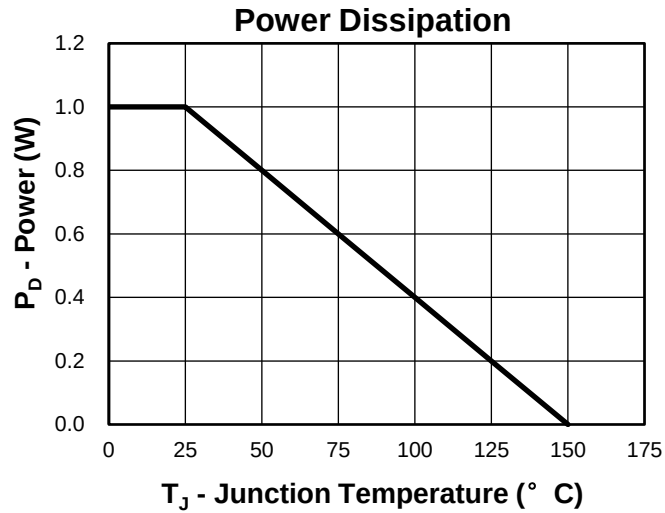
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS4244AA	SOT23	Tape&Reel	3000	7"	8mm



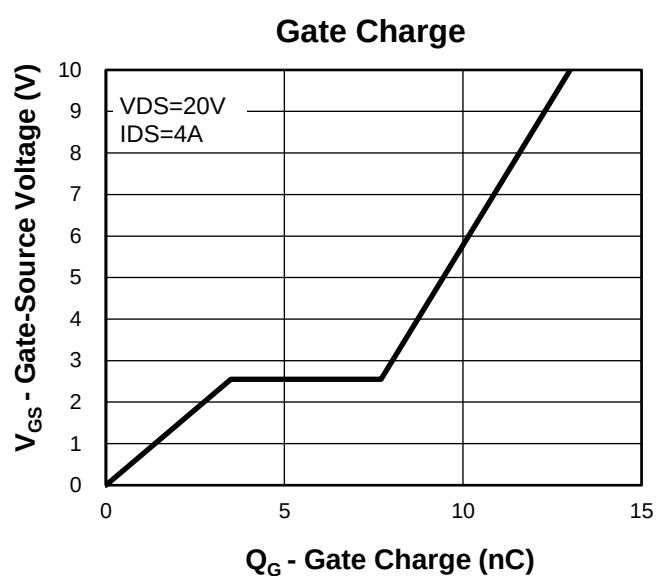
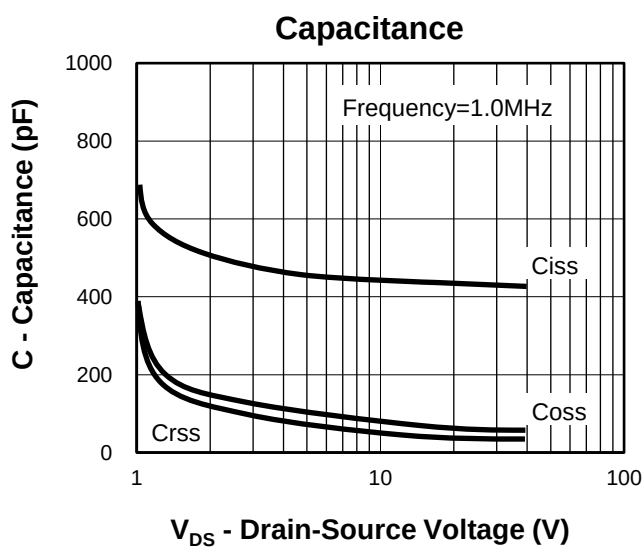
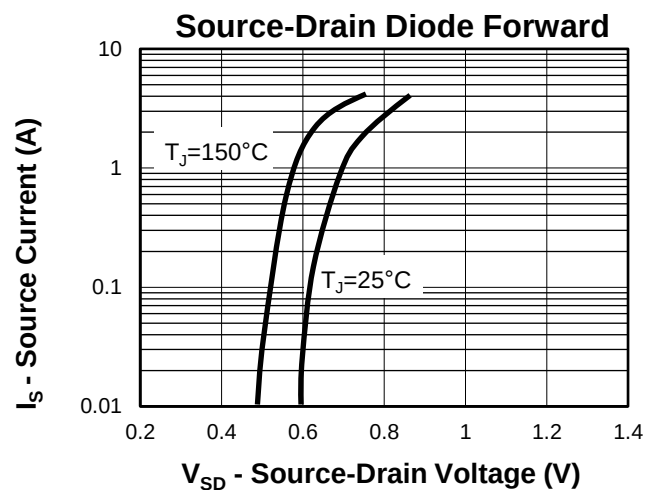
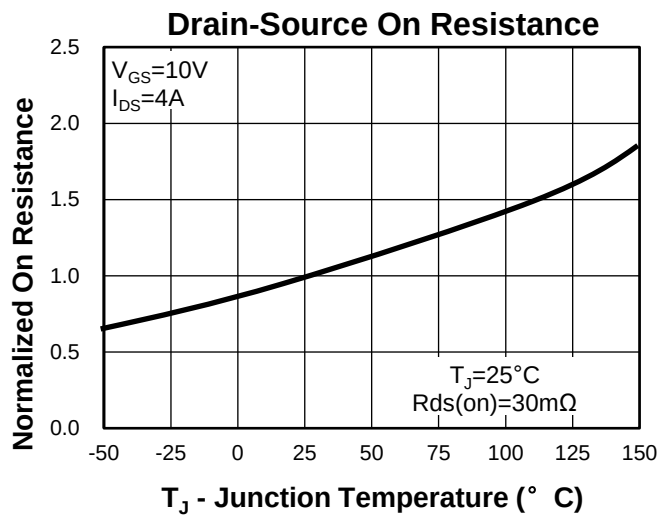
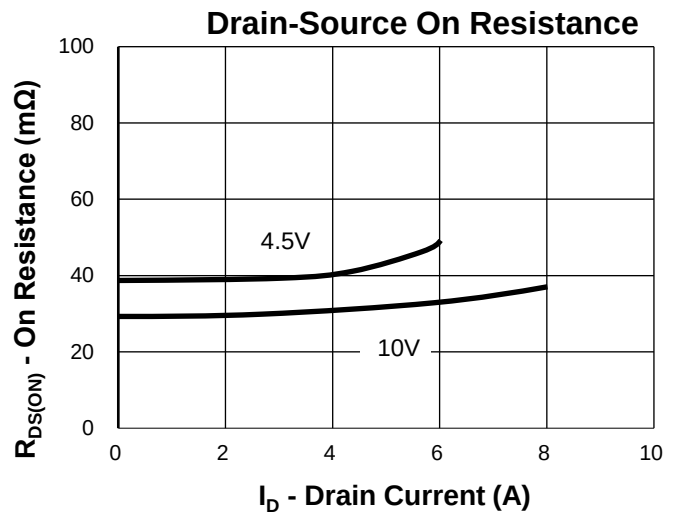
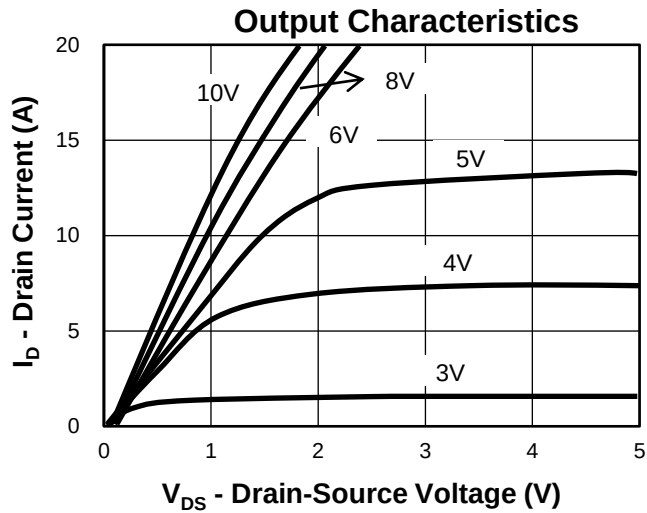
Y =Year,2017-A,2018-B,etc.

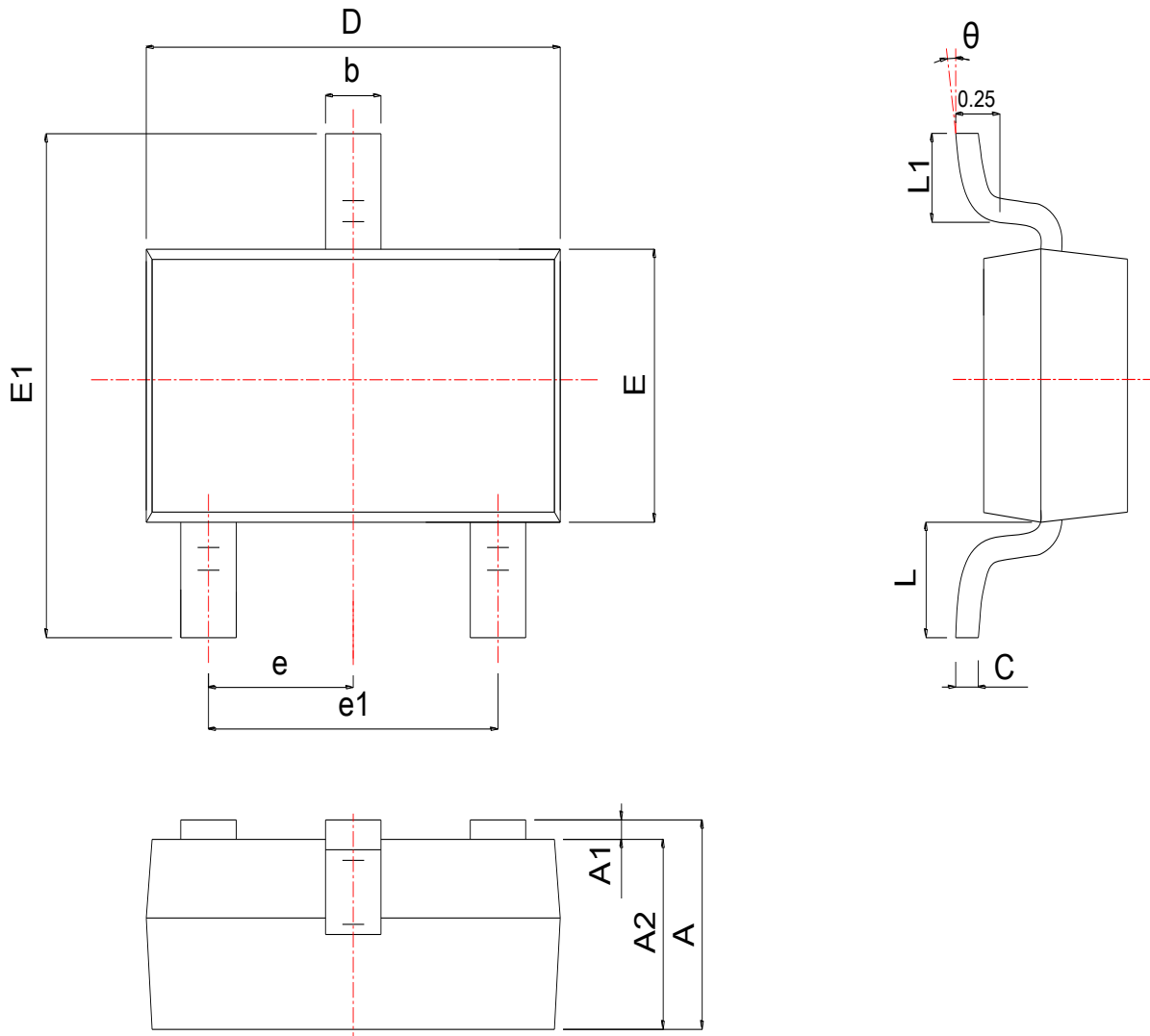
M =Month,Jan-1,Feb-2,....Sep-9,Oct-A,Nov-B,Dec-C.

Typical Characteristics



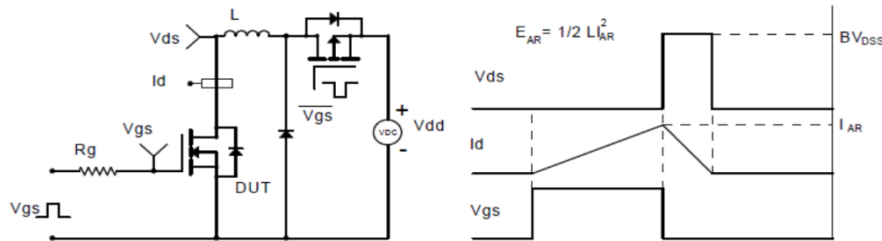
Typical Characteristics



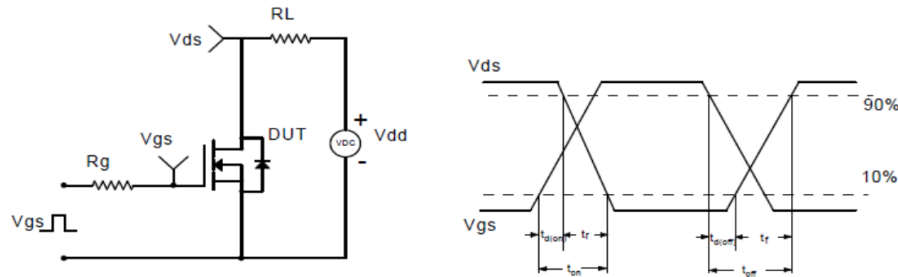
Package Information
SOT23


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.900	1.025	1.150	0.035	0.040	0.045
A1	0.050	0.075	0.100	0.002	0.003	0.004
A2	0.900	0.975	1.020	0.035	0.038	0.040
b	0.300	0.400	0.500	0.012	0.016	0.020
c	0.080	0.115	0.150	0.003	0.005	0.006
D	2.800	2.900	3.000	0.110	0.114	0.118
E	1.200	1.300	1.400	0.047	0.051	0.055
E1	2.250	2.400	2.550	0.089	0.094	0.100
e	0.950 TYP			0.037 TYP		
e1	1.800	1.900	2.000	0.071	0.075	0.079
L	0.540 REF			0.021 REF		
L1	0.400	0.500	0.600	0.016	0.018	0.020
θ	0°	*	8°	0°	*	8°

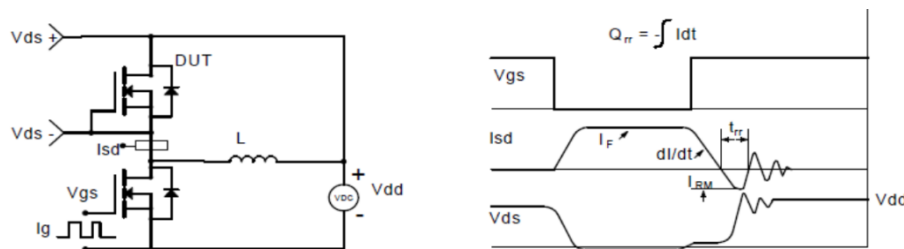
Avalanche Test Circuit and Waveforms



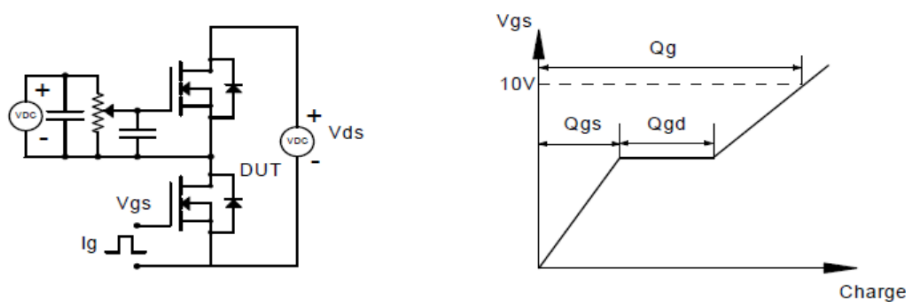
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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